

UNITED STATES DEPARTMENT OF COMMERCE

United States Patent and Trademark Office

Address: COMMISSIONER OF PATENTS AND TRADEMARKS

Washington, D.C. 20231

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTO	R	ATTORNEY DOCKET NO.
09/450.351	11/29/99	YAMAMOTO	T	SHM-00901
026339		MMC1/0828		EXAMINER
HUTCHINS, WHEELER & DITTMAR			าร	AI.H
101 FEDERA BOSTON MA			ART U	NIT PAPER NUMBER
POSTON IN	OZIIO		28	12
			DATE MAII	LED: 08/28/01

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks

Application No. 09/450,351

Applicant(s)

Yamamoto

Office Ac	tion Su	<i>ımmar</i> y	/
-----------	---------	----------------	---

Examiner
H. Jey Tsai

Art Unit **2812**

The MAILING DATE of this communication appears on the cover sheet with the correspondence address				
communication Failure to reply within the set or extended period for reply will, by	R 1.136 (a). In no event, however, may a reply be timely filed tion. a reply within the statutory minimum of thirty (30) days will eriod will apply and will expire SIX (6) MONTHS from the mailing date of this statute, cause the application to become ABANDONED (35 U.S.C. § 133). mailing date of this communication, even if timely filed, may reduce any			
	cept for formal matters, prosecution as to the merits is			
closed in accordance with the practice under Ex par	te Quayle, 1935 C.D. 11; 453 O.G. 213.			
Disposition of Claims	is to a south a time the southerstand			
	is/are pending in the application.			
	is/are withdrawn from consideration.			
5) Claim(s)	is/are allowed.			
6) 💢 Claim(s) <u>1-11 and 13-29</u>	is/are rejected.			
7) Claim(s)	is/are objected to.			
8) Claims	are subject to restriction and/or election requirement.			
Application Papers 9) The specification is objected to by the Examiner. 10) The drawing(s) filed on is/are 11) The proposed drawing correction filed on 12) The oath or declaration is objected to by the Examin	is: a) □ approved b) □ disapproved.			
_	e been received. e been received in Application No cuments have been received in this National Stage lu (PCT Rule 17.2(a)). e certified copies not received.			
Attachment(s)				
	18) Interview Summary (PTO-413) Paper No(s).			
	19) Notice of Informal Patent Application (PTO-152) Other:			

Art Unit: 2812

Claim Rejections - 35 U.S.C. § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-11 and 13-29 stand rejected under 35 U.S.C. 103(a) as being unpatentable over Tamaru et al. 6,103,566 in view of Nishikawa 6,087,261 and Lee et al. 6,010,940, all are previously applied.

The reference(s) teach the features:

Tamaru et al. substantially discloses a method of forming a capacitor on the semiconductor device, which includes :

forming a tantalum oxide dielectric layer 5, fig. 4B, and col. 16, lines 7+,

treating substrate in the chamber with at least one of a gas containing non-reactive helium or Ar or N_2 gas and NH_3 ,

heating the substrate in the NH₃ col. 9, lines 44+,

Art Unit: 2812

Nishikawa substantially discloses a method of forming a capacitor on the semiconductor device, which includes:

forming a tantalum oxide dielectric layer 5, fig. 4B, treating substrate in the chamber with at least one of a gas containing non-reactive NH_3 and helium gases flow, col. 9, lines 1+,

heating the substrate in the $\mathrm{NH_3}$ ambient at about 0.15 torr, fig. 6, col. 9, lines 30+,

The difference between the reference(s) and the claims are as follows:

Tamaru et al. lacks vacuum pressure. However, Nishikawa teaches heating the substrate in the $\mathrm{NH_3}$ ambient at about 0.15 torr, fig. 6, col. 9, lines 30+. And, Lee teaches annealing the substrate with $\mathrm{NH_3}$ after forming TiN.

It would have been obvious to one having ordinary skill in the art at the time the invention was made to have modified Tamaru's vacuum pressure at less than 1 because a better non-reactive ambient can be obtained at the lower the vacuum pressure.

Art Unit: 2812

Applicant's arguments filed Aug. 3, 2001 have been fully considered but they are not persuasive.

Applicant contends that Nishikawa teaches using an oxidizing ambient and not an inert ambient. This is not found to be persuasive because 1). Tamaru's teaching containing only Ar or N2 or He. 2). Since claimed invention containing reactive gas NH₃, hence, the limitation of non-reactive with respect to metal oxide is not consistent with the claimed invention. Nishikawa teaches one of gases is helium gas which is an inert gas, hence is non-reactive with respect to the tantalum oxide layer 5, therefore, it meets the claimed invention. see col. 9, lines 13+,

Applicant contends that Nishikawa teaches introduing He and oxygen prior to the deposition of metal oxide during the a chamber purging step. This is not found to be persuasive because Nishikawa teaches reduction or reoxidation of Ta_sO_5 by introducing oxygen and helium is prevented in col. 9, lines 12+. And, oxygne only react with the carbon or hydrogen in the Ta_sO_5 layer not Ta_sO_5 layer itself. Tamaru et al. meets every limitation as claimed in claim 1 and Nishikawa meets every limitation as claimed in claim 8.

Any inquiry of a general nature or clerical matters or relating to the status of this application or proceeding should be directed to the Group customer service whose telephone number

Art Unit: 2812

is (703) 306-3329 and Fax number (703) 306-5515. Group receptionist telephone number 703-308-0956.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to H. Jey Tsai whose telephone number is (703) 308-1374. The examiner can normally be reached on from 7:00 Am to 4:00 Pm., Monday thru Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on (703) 308-3325. The fax phone number for this Group is (703) 305-3431.

hjt 08/26/1

> H. Jeý Tsai Primary Examiner

Patent Examining Group 2800